

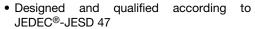
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# Thyristor High Voltage, Phase Control SCR, 10 A

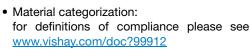


PRIMARY CHARACTERISTICS							
I <sub>T(AV)</sub>	6.5 A						
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V						
V <sub>TM</sub>	1.15 V						
I <sub>GT</sub>	15 mA						
T <sub>J</sub>	-40 °C to 125 °C						
Package	TO-220AB 3L						
Circuit configuration	Single SCR						

#### **FEATURES**









#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft star) and AC switch in motor control, UPS, welding, and battery charge

#### **DESCRIPTION**

The VS-10TTS08... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS										
APPLICATIONS	PPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
Capacitive input filter  T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C,  common heatsink of 1 °C/W	13.5	17	А							

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I <sub>T(AV)</sub>	Sinusoidal waveform	6.5	۸						
I <sub>T(RMS)</sub>		10	Α						
V <sub>RRM</sub> /V <sub>DRM</sub>		800	V						
I <sub>TSM</sub>		110	А						
V <sub>T</sub>	6.5 A, T <sub>J</sub> = 25 °C	1.15	V						
dV/dt		150	V/µs						
dl/dt		100	A/µs						
T <sub>J</sub>	Range	-40 to +125	°C						

<b>VOLTAGE RATINGS</b>			
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA
VS-10TTS08-M3	800	800	1.0



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ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS			
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 112 °C, 180° conduction half sine wave		6.5	•			
Maximum RMS on-state current	I <sub>T(RMS)</sub>	1 <sub>C</sub> = 112 C, 180 Conduc	ction hall sine wave	10				
Maximum peak, one-cycle,		10 ms sine pulse, rated V	<sub>RRM</sub> applied, T <sub>J</sub> = 125 °C	95	Α			
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no volta	age reapplied, T <sub>J</sub> = 125 °C	110				
Maximum 12t for finning	I <sup>2</sup> t	10 ms sine pulse, rated V	<sub>RRM</sub> applied, T <sub>J</sub> = 125 °C	45	A <sup>2</sup> s			
Maximum I <sup>2</sup> t for fusing	1-1	10 ms sine pulse, no volta	age reapplied, T <sub>J</sub> = 125 °C	64				
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 ms to 10 ms, no vo	640	A²√s				
Maximum on-state voltage drop	$V_{TM}$	6.5 A, T <sub>J</sub> = 25 °C	1.15	V				
On-state slope resistance	r <sub>t</sub>	T 405.00		17.3	mΩ			
Threshold voltage	V <sub>T(TO)</sub>	- T <sub>J</sub> = 125 °C		0.85	V			
Maximum reverse and direct leakage	1 /1	T <sub>J</sub> = 25 °C	V Dated V A/	0.05				
current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	$V_R = Rated V_{RRM}/V_{DRM}$	1.0				
Typical holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C		30	mA			
Maximum latching current	ال	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C		50				
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80$	T <sub>J</sub> = T <sub>J</sub> max., linear to 80 %, V <sub>DRM</sub> = R <sub>g</sub> - k = Open					
Maximum rate of rise of turned-on current	dl/dt			100	A/µs			

TRIGGERING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum peak gate power	$P_{GM}$		8.0	W					
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV					
Maximum peak positive gate current	+I <sub>GM</sub>		1.5	Α					
Maximum peak negative gate voltage	-V <sub>GM</sub>		10	V					
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	20						
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	15	mA					
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	10						
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	1.2						
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	1	v					
voltage to anggor		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	0.7	V					
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V Detect value	0.2	]					
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	0.1	mA					

SWITCHING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.8						
Typical reverse recovery time	t <sub>rr</sub>	T 105 °C	3	μs					
Typical turn-off time	t <sub>q</sub>	T <sub>J</sub> = 125 °C	100						



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THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C				
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation	1.5					
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W				
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.5					
Annewinesta weight				2	g				
Approximate weight				0.07	oz.				
Maunting targue	minimum			6 (5)	kgf · cm				
Mounting torque -	maximum			12 (10)	(lbf · in)				
Marking device			Case style TO-220AB 3L	10TTS	308				

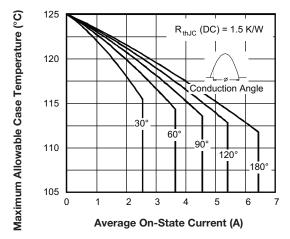


Fig. 1 - Current Rating Characteristics

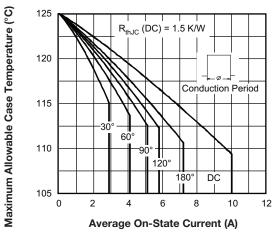


Fig. 2 - Current Rating Characteristic

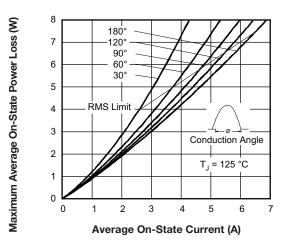


Fig. 3 - On-State Power Loss Characteristics

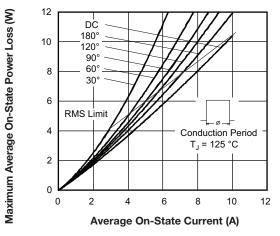


Fig. 4 - On-State Power Loss Characteristics

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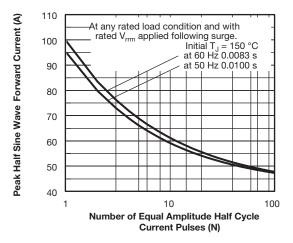


Fig. 5 - Maximum Non-Repetitive Surge Current

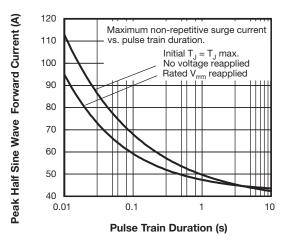


Fig. 6 - Maximum Non-Repetitive Surge Current

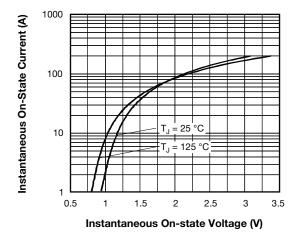


Fig. 7 - On-State Voltage Drop Characteristics

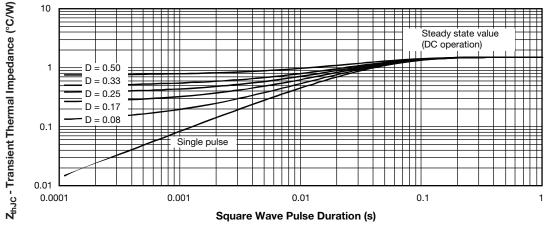


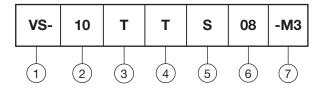
Fig. 8 - Thermal Impedance ZthJC Characteristics



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### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Current rating

3 - Circuit configuration:

T = single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

S = converter grade

6 - Voltage code x 100 = V<sub>RRM</sub>

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	EFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION							
VS-10TTS08-M3	50	Antistatic plastic tubes						

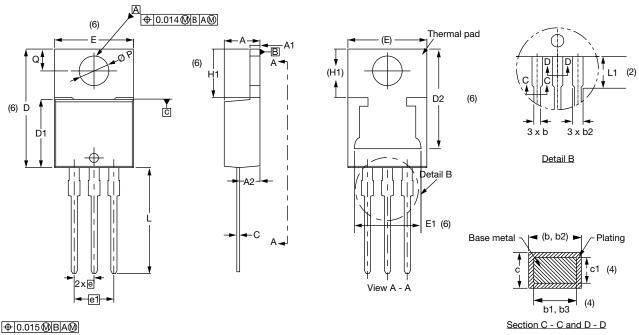
LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?96154						
Part marking information	www.vishay.com/doc?95028					

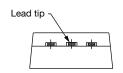


## Vishay Semiconductors

### **TO-220AB 3L**

#### **DIMENSIONS** in millimeters and inches





Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIM	IETERS	INCHES		NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			Е	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355								

### **Notes**

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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